# CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17



# MAULANA ABUL KALAM AZAD UNIVERSITY OF TECHNOLOGY, WEST BENGAL

Paper Code: EC-702

# MICROELECTRONICS & VLSI DESIGNS

, Time Allotted: 3 Hours

Full Marks: 70

http://www.makaut.com

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

# GROUP - A ( Multiple Choice Type Questions )

- 1. Choose the correct alternatives for any ten of the following:  $10 \times 1 = 10$ 
  - i) In which device has the highest carrier mobility?
    - a) NMOS
    - b) PMOS
    - of CMOS.
  - ii) Which device acts as good switch?
    - a) NMOS
    - b) PMOS
    - cy CMOS.

7/70103

http://www.makaut.com

[ Turn over

CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17

iii) In which device at zero gate voltage the channel already exist?

a) Depletion type MOSFET

- b) CMOS device
- c) Enhance type MOSFET.
- iv) The condition, where the majority carrier concentration is greater near the Si-SiO 2 interface compared to the bulk in the MOSFET is called

a) Accumulation

b) Depletion

c) Inversion.

- v) The potential at which the inversion layer dominates the substrate behaviour is
  - a) Pinch-off voltage
  - b) Cut-off voltage

c) Threshold voltage.

7/70103

2

# CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17

- vi) The overlap capacitance is
  - a) voltage dependent
  - b) voltage independent
  - c) none of these.
- vii) Which has highest noise margin?
  - a) active load inverter
  - b) resistive load inverter
  - c) CMOS inverter.
- viii) Which is correct for the accumulation region?
  - a)  $V_{GB} < V_{FB}$

- c)  $V_{GB} = V_{FB}$ .
- ix) The static power dissipation is NIL for
  - a) single transistor dynamic RAM
  - b) Pseudo-static RAM

Static RAM.

0103 3

http://www.makaut.com

[ Turn over

# CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17

- x) Which design is more efficient?
  - a) Pull up & Pull down design

b) TG design

- c) Pre-charge & evaluate logic.
- xi) Overlapping capacitance of MOS denotes
  - a) capacitance between drain and oxide layer
  - b) capacitance between source and oxide layer
  - cy both (a) and (b).

#### **GROUP - B**

# (Short Answer Type Questions)

Answer any three of the following.  $3 \times 5 = 15$ 

- 2/ Explain the following phenomena in a MOS structure :
  - a) Channel length modulation
  - b) Scaling of MOSFET.

.2 + 3

- 3, a) Explain the working principle of a CMOS inverter.
  - b) Draw the VTC curve of a simple CMOS inverter circuit and clearly define the different operating regions of NMOS and PMOS.
    2+3

7/70103

http://www.makaut.com

http://www.makaut.com

- 4. What is modularity and locality of VLSI design?
- Design a half subtractor circuit using PLA.
- Design a PROM which takes 3 binary bits as input and generates the output which is the square of the input.

#### GROUP - C

### (Long Answer Type Questions)

Answer any three of the following.  $3 \times 15 = 45$ 

- 7. a) What is "divide and conquer method"? Explain.
  - b) Draw the layout and schematic diagram of a 2-input static CMOS NAND gate and clearly identify the corresponding components in the two drawings.
  - c) With suitable diagram briefly describe the p-well fabrication process of a CMOS inverter.
  - d) What is micron rule?

7/70103 5 [ Turn over

2+5+6+2

# CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17

- a) Design a CMOS half adder using smallest possible number of transistors.
  - b) Draw a clocked D flip-flop using CMOS and explain.
  - Design a transmission Gate based XNOR gate using six transistors.
  - d) What is pseudo-NMOS logic?

6+4+3+2

- a) Distinguish between diffusion and ion-implatation technique.
- b) What is photolithography? Explain.
- c) What is meant by Molecular Beam Epitaxy (MBE)?
- d) Explain how MOSFET can be used as resistor.

4+5+3+3

- a) What is current mirror ? Explain with proper circuit diagram.
  - b) Draw the block diagram of a two-stage op-amp and explain the function of each block.
  - c) How can you realize the resistor using switched capacitor circuits?
  - d) What is switched capacitor filter ? (1 + 3) + 5 + 4 + 2

7/70103

http://www.makaut.com

9.

6

http://www.makaut.com

## CS/B.TECH/ECE/ODD SEM/SEM-7/EC-702/2016-17

11. Write short notes on any three of the following:  $3 \times 5$ 

- a) FPGA
  - b) MOS capacitor
  - c) Programmable Logic Array
  - d) Ion Implantation
- el Czochralski technique for crystal growth
- f) Y chart of VLSI design flow.

ппр://www.maкапг.com

7/70103

http://www.makaut.com

7